

ERRATUM

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Erratum to: Optical properties and bandgap evolution of ALD HfSiO_x films

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The authors of *Nanoscale Research Letters* 2015, 10:32 (DOI 10.1186/s11671-014-0724-z) [1] omitted to acknowledge that all ellipsometric data discussed in the article, including those displayed in Figure 1, were recorded in the laboratory of the Semiconductor Physics Group, Institut für Experimentelle Physik, Universität Leipzig, with the active involvement and under the guidance of Tammo Böntgen, Rüdiger Schmidt-Grund, and Marius Grundmann.

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Received: 3 September 2015 Accepted: 16 September 2015

Published online: 29 September 2015

Reference

1. Yang W, Fronk M, Geng Y, Chen L, Sun QQ, Gordan OD, et al. Optical properties and bandgap evolution of ALD HfSiO_x films. *Nanoscale Res Lett*. 2015;10:32.

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